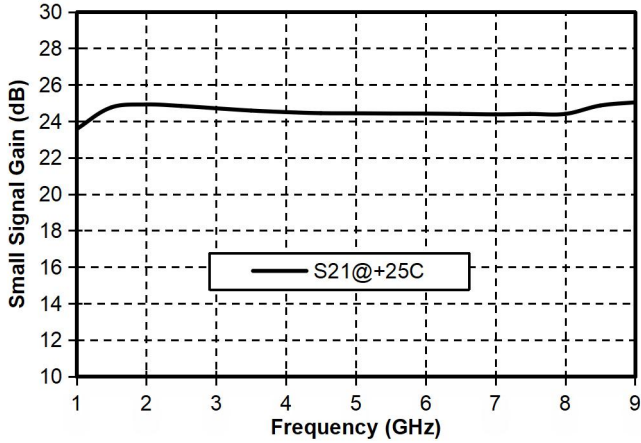


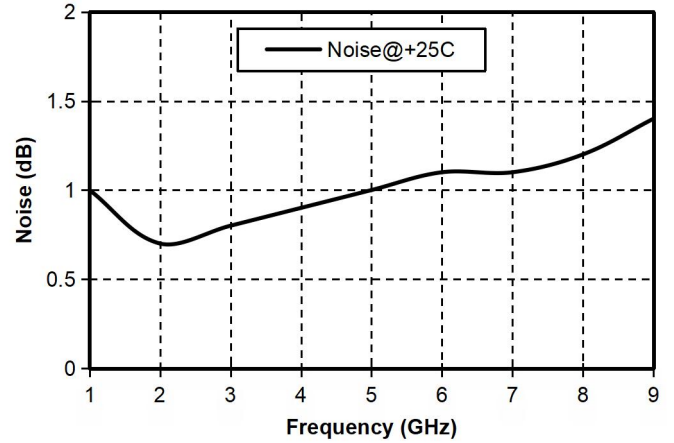
GaAs MMIC Low Noise Amplifier Chip, 1-9 GHz

Main index test curve

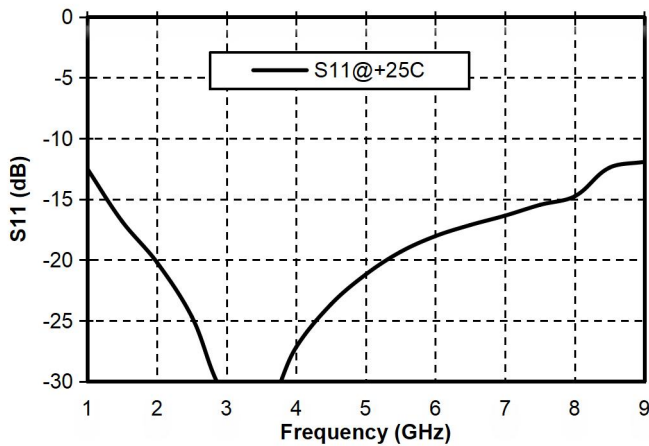
Gain vs. Frequency



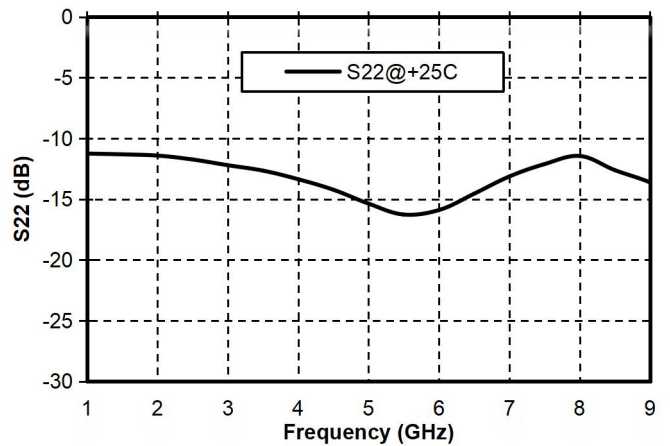
Noise Figure vs. Frequency



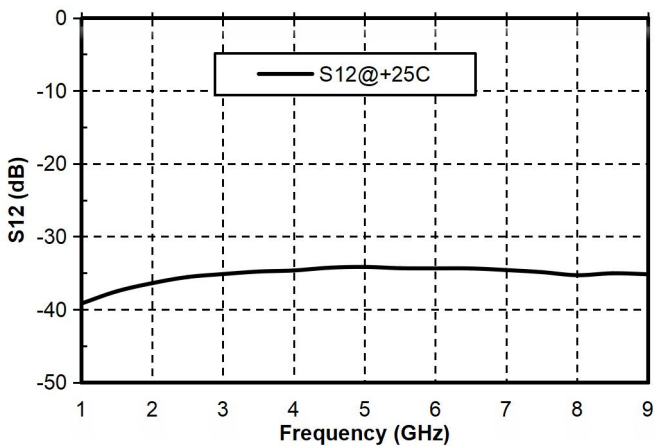
Input Return Loss vs. Frequency



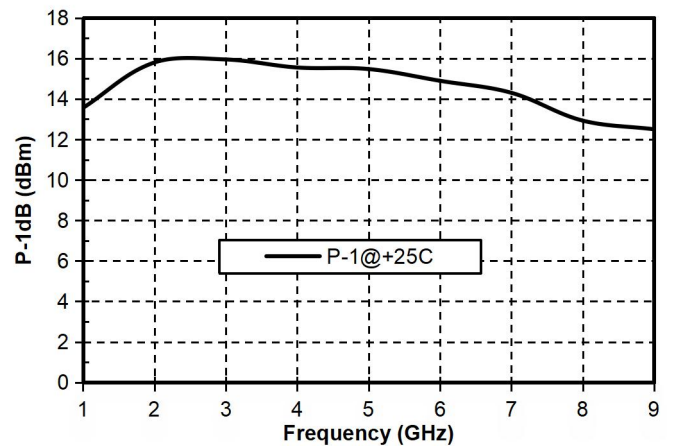
Output Return Loss vs. Frequency



Reverse Isolation vs. Frequency

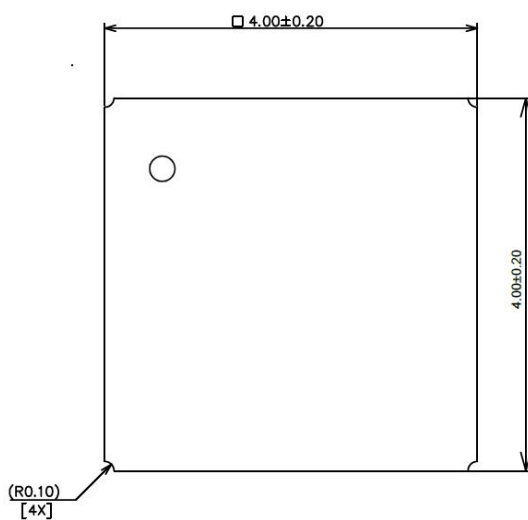


P-1dB vs. Frequency

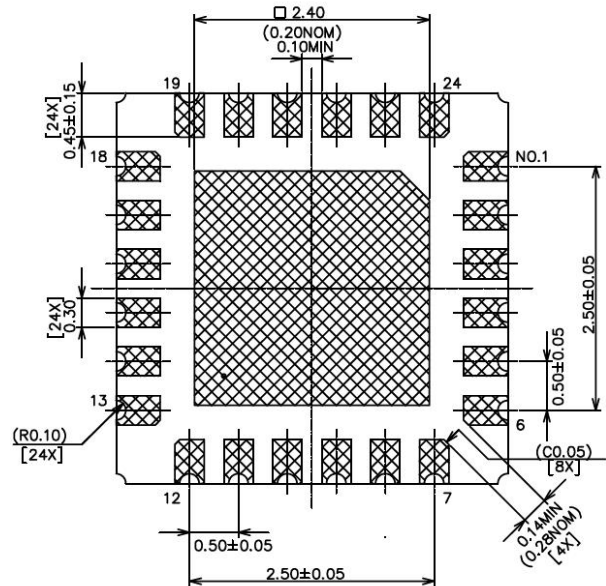


GaAs MMIC Low Noise Amplifier Chip, 1-9 GHz

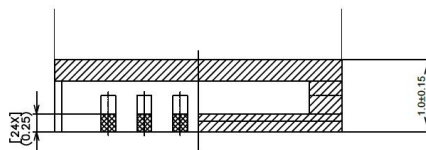
Appearance structure



Top view



Bottom view



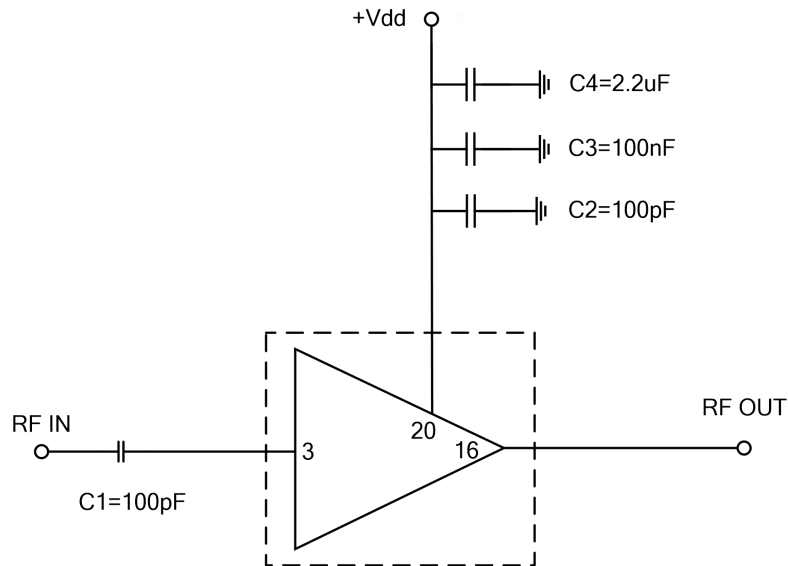
Side View

All units in the figures are millimeters .

| Pin Definition | | |
|------------------------|-----------------|---|
| Bonding point number | Function Symbol | Functional Description |
| 3 | RFIN | RF signal input terminal, requires DC blocking capacitor |
| 16 | RFOUT | RF signal output terminal, no DC blocking capacitor required |
| 20 | VDD | Amplifier Drain Bias |
| 2, 4, 15, 17 | GND | The bottom of the chip needs to be well grounded to RF and DC |
| 1, 5~14, 18, 19, 21~24 | NC | No welding required |

GaAs MMIC Low Noise Amplifier Chip, 1-9 GHz

Recommended Circuit



| Raw material | Capacitance, inductance, resistance |
|--------------|-------------------------------------|
| C1 | 100pF |
| C2 | 100pF |
| C3 | 100nF |
| C4 | 2.2uF |

Precautions for use

- Sealing material : Ceramic material that meets ROHS standards
- Lead frame material: copper alloy
- Lead surface plating: gold, gold layer thickness greater than 1.5um
- Maximum reflow peak temperature: 260°C